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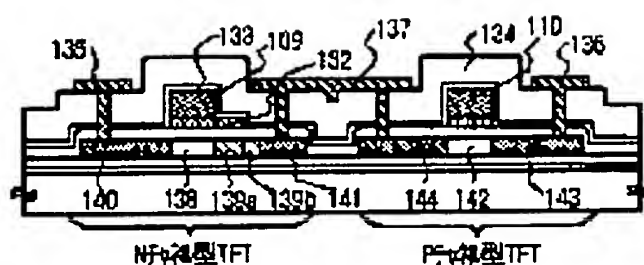
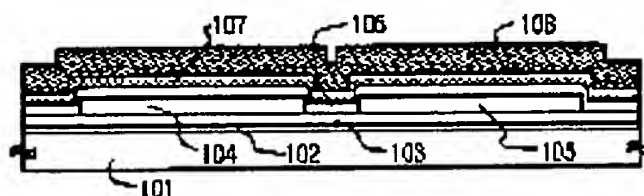
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(54) SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

PROBLEM TO BE SOLVED: To obtain good characteristics in both states of ON and OFF, by allowing a gate electrode to have the first and second layers, a semiconductor layer to have a channel forming region, a first and second impurity regions, and a part 1 of the second impurity region to be overlaid with the first layer of the gate electrode.

SOLUTION: A first conductive film 107 to be the first layer of a gate electrode and a second conductive layer 108 to be the second layer of the gate electrode are formed on the surface of a gate insulating film 106. The first conductive film 107 is a semiconductor film containing Si or Ge as a main component. The second conductive film 108 contains Ti, Ta, W and Mo as main components. A channel forming region 138, first impurity regions 140, 141 and a second impurity region are formed in an n-channel TFT (a thin film transistor) of a CMOS circuit. Here, in the second impurity region, a region 139a (GOLD region) which superimposes with the gate electrode and a region 139b (LDD region) which does not overlap the gate electrode are respectively formed.



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